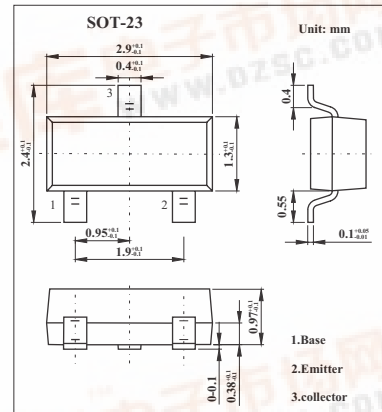


SMD Type Transistors

Silicon PNP Triple Diffused Type
2SA1255

■ Features

- High voltage.
- Small package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-200	V
Collector-emitter voltage	V _{CEO}	-200	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-50	mA
Base current	I _B	-20	mA
Collector power dissipation	P _c	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I _{cBO}	V _{CB} = -200 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-0.1	μA
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1 mA, I _E = 0	-200			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1 mA, I _B = 0	-200			V
DC current gain	h _{FE}	V _{CE} = -3 V, I _C = -10 mA	70		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -1 mA		-0.2	-1	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -10 mA, I _B = -1 mA		-0.75	-1.5	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -2 mA	50	100		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz		3	7	pF
Turn-on time	t _{on}	pulse width = 5μs, duty cycle ≤ 2%		0.3		μs
Storage time	t _{stg}	I _{B2} = -I _{B1} = 0.6 Ma		2		μs
Fall time	t _f	V _{CC} = -50V, I _C = -6mA		0.4		μs

■ hFE Classification

Marking	OO	OY
Rank	O	Y
hFE	70~140	120~240

